

Frank Bertram

List of Publications by Year in descending order

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197
papers

5,579
citations

109321

35
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91884

69
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201
all docs

201
docs citations

201
times ranked

5306
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 1 | Desorption induced formation of low-density GaN quantum dots: nanoscale correlation of structural and optical properties. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 145102. | 2.8 | 0 |
| 2 | Direct Imaging of the Carrier Capture into Individual InP Quantum Dots of a Semiconductor Disk Laser Membrane. <i>ACS Nano</i> , 2022, 16, 4619-4628. | 14.6 | 0 |
| 3 | Correlating yellow and blue luminescence with carbon doping in GaN. <i>Journal of Crystal Growth</i> , 2022, 586, 126634. | 1.5 | 2 |
| 4 | Color-tunable 3D InGaN/GaN Multi-Quantum-Well Light-Emitting Diode Based on Microfacet Emission and Programmable Driving Power Supply. <i>Advanced Optical Materials</i> , 2021, 9, . | 7.3 | 14 |
| 5 | Characteristic emission from quantum dot-like intersection nodes of dislocations in GaN. <i>Journal of Physics: Conference Series</i> , 2021, 1851, 012013. | 0.4 | 1 |
| 6 | Demonstration of lateral epitaxial growth of AlN on Si (1 1 1) at low temperatures by pulsed reactive sputter epitaxy. <i>Journal of Crystal Growth</i> , 2021, 571, 126250. | 1.5 | 6 |
| 7 | Cathodoluminescence nano-characterization of individual GaN/AlN quantum disks embedded in nanowires. <i>Applied Physics Letters</i> , 2020, 117, 133106. | 3.3 | 3 |
| 8 | Thermally annealed wafer-scale h-BN films grown on sapphire substrate by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2020, 116, . | 3.3 | 16 |
| 9 | Optical and Structural Properties of Nitride Based Nanostructures. <i>Springer Series in Solid-state Sciences</i> , 2020, , 135-201. | 0.3 | 2 |
| 10 | Individually resolved luminescence from closely stacked GaN/AlN quantum wells. <i>Photonics Research</i> , 2020, 8, 610. | 7.0 | 8 |
| 11 | Nitride Microcavities and Single Quantum Dots for Classical and Non-classical Light Emitters. <i>Springer Series in Solid-state Sciences</i> , 2020, , 453-504. | 0.3 | 1 |
| 12 | Ordered arrays of defect-free GaN nanocolumns with very narrow excitonic emission line width. <i>Journal of Crystal Growth</i> , 2019, 525, 125189. | 1.5 | 7 |
| 13 | Intensive luminescence from a thick, indium-rich In _{0.7} Ga _{0.3} N film. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 065503. | 1.5 | 2 |
| 14 | Nanoscale mapping of carrier recombination in GaAs/AlGaAs core-multishell nanowires by cathodoluminescence imaging in a scanning transmission electron microscope. <i>Applied Physics Letters</i> , 2019, 115, 243102. | 3.3 | 4 |
| 15 | Surface development of a brazing alloy during heat treatment—a comparison between UHV and APXPS. <i>Journal of Physics Condensed Matter</i> , 2018, 30, 024004. | 1.8 | 2 |
| 16 | Direct imaging of Indium-rich triangular nanoprisms self-organized formed at the edges of InGaN/GaN core-shell nanorods. <i>Scientific Reports</i> , 2018, 8, 16026. | 3.3 | 19 |
| 17 | MOVPE-growth of InGaSb/AlP/GaP(001) Quantum Dots for Nanoscale Memory Applications. <i>Physica Status Solidi (B): Basic Research</i> , 2018, 255, 1800182. | 1.5 | 24 |
| 18 | Recent progress in nonpolar and semi-polar GaN light emitters on patterned Si substrates. , 2018, , . | | 3 |

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|----|---|-----|-----------|
| 19 | Compositionally graded InGaN layers grown on vicinal N-face GaN substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017, 465, 55-59. | 1.5 | 16 |
| 20 | Theoretical study of time-resolved luminescence in semiconductors. IV. Lateral inhomogeneities. <i>Journal of Applied Physics</i> , 2017, 121, . | 2.5 | 11 |
| 21 | Emission of Linearly Polarized Single Photons from Quantum Dots Contained in Nonpolar, Semipolar, and Polar Sections of Pencil-Like InGaN/GaN Nanowires. <i>ACS Photonics</i> , 2017, 4, 657-664. | 6.6 | 44 |
| 22 | Exciton emission of quasi-2D InGaN in GaN matrix grown by molecular beam epitaxy. <i>Scientific Reports</i> , 2017, 7, 46420. | 3.3 | 14 |
| 23 | Selective area growth of AlN/GaN nanocolumns on (0001) and (11 $\bar{2}$) GaN/sapphire for semi-polar and non-polar AlN pseudo-templates. <i>Nanotechnology</i> , 2017, 28, 365704. | 2.6 | 6 |
| 24 | Nanometer-scale Resolved Cathodoluminescence Imaging: New Insights into GaAs/AlGaAs Core-shell Nanowire Lasers. <i>Microscopy and Microanalysis</i> , 2017, 23, 1470-1471. | 0.4 | 0 |
| 25 | Surface development of an aluminum brazing sheet during heating studied by XPEEM and XPS. <i>Materials Research Express</i> , 2016, 3, 106506. | 1.6 | 5 |
| 26 | Improvement of optical quality of semipolar (112 $\bar{2}$) GaN on <i>m</i> -plane sapphire by <i>in-situ</i> epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 2016, 119, . | 2.5 | 12 |
| 27 | Direct correlations of structural and optical properties of three-dimensional GaN/InGaN core/shell micro-light emitting diodes. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FJ09. | 1.5 | 22 |
| 28 | Nanoscale Insights into InGaN/GaN Core-Shell Nanorods: Structure, Composition, and Luminescence. <i>Nano Letters</i> , 2016, 16, 5340-5346. | 9.1 | 43 |
| 29 | Embedded GaN nanostripes on <i>c</i> -sapphire for DFB lasers with semipolar quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 180-185. | 1.5 | 5 |
| 30 | Defect reduced selectively grown GaN pyramids as template for green InGaN quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 67-72. | 1.5 | 2 |
| 31 | Polarization engineering of <i>c</i> -plane InGaN quantum wells by pulsed-flow growth of AlInGaN barriers. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 118-125. | 1.5 | 6 |
| 32 | Nanoscale cathodoluminescence of stacking faults and partial dislocations in <i>a</i> -plane GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 73-77. | 1.5 | 2 |
| 33 | Direct microscopic correlation of real structure and optical properties of semipolar GaN based on pre-patterned <i>r</i> -plane sapphire. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 54-60. | 1.5 | 1 |
| 34 | Nanoscale cathodoluminescence imaging of III-nitride-based LEDs with semipolar quantum wells in a scanning transmission electron microscope. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 112-117. | 1.5 | 7 |
| 35 | Microscopic nature of crystal phase quantum dots in ultrathin GaAs nanowires by nanoscale luminescence characterization. <i>New Journal of Physics</i> , 2016, 18, 063009. | 2.9 | 12 |
| 36 | Influence of composition, strain, and electric field anisotropy on different emission colors and recombination dynamics from InGaN nanodisks in pencil-like GaN nanowires. <i>Physical Review B</i> , 2016, 93, . | 3.2 | 18 |

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| 37 | Structural and optical nanoscale analysis of GaN core-shell microrod arrays fabricated by combined top-down and bottom-up process on Si(111). Japanese Journal of Applied Physics, 2016, 55, 05FF02. | 1.5 | 4 |
| 38 | Clustered quantum dots in single GaN islands formed at threading dislocations. Japanese Journal of Applied Physics, 2016, 55, 05FF04. | 1.5 | 5 |
| 39 | Phosphor-converted white light from blue-emitting InGaN microrod LEDs. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1577-1584. | 1.8 | 48 |
| 40 | Direct evidence of single quantum dot emission from GaN islands formed at threading dislocations using nanoscale cathodoluminescence: A source of single photons in the ultraviolet. Applied Physics Letters, 2015, 106, . | 3.3 | 29 |
| 41 | Determination of carrier diffusion length in GaN. Journal of Applied Physics, 2015, 117, . | 2.5 | 33 |
| 42 | STEM-CL investigations on the influence of stacking faults on the optical emission of cubic GaN epilayers and cubic GaN/AlN multi-quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 469-472. | 0.8 | 18 |
| 43 | Optical Emission of Individual GaN Nanocolumns Analyzed with High Spatial Resolution. Nano Letters, 2015, 15, 5105-5109. | 9.1 | 35 |
| 44 | Enhancement of optical and structural quality of semipolar (11-22) GaN by introducing nanoporous SiNx interlayers. , 2015, , . | | 2 |
| 45 | Indium-incorporation efficiency in semipolar (11-22) oriented InGaN-based light emitting diodes. , 2015, , . | | 6 |
| 46 | The thickness of native oxides on aluminum alloys and single crystals. Applied Surface Science, 2015, 349, 826-832. | 6.1 | 174 |
| 47 | Ordered arrays of InGaN/GaN dot-in-a-wire nanostructures as single photon emitters. Proceedings of SPIE, 2015, , . | 0.8 | 10 |
| 48 | Strong exciton-photon coupling in hybrid InGaN-based microcavities on GaN substrates. Proceedings of SPIE, 2015, , . | 0.8 | 0 |
| 49 | Blue-to-green single photons from InGaN/GaN dot-in-a-nanowire ordered arrays. Europhysics Letters, 2015, 111, 24001. | 2.0 | 24 |
| 50 | Gallium gradients in Cu(In,Ga)Se ₂ thin-film solar cells. Progress in Photovoltaics: Research and Applications, 2015, 23, 717-733. | 8.1 | 122 |
| 51 | Nanoscale Characterization of Structural and Optical Properties of Nitride Nanostructures Using Helium Temperature Scanning Electron Microscopy Cathodoluminescence. , 2014, , . | | 0 |
| 52 | Advances in MBE Selective Area Growth of III-Nitride Nanostructures: From NanoLEDs to Pseudo Substrates. International Journal of High Speed Electronics and Systems, 2014, 23, 1450020. | 0.7 | 4 |
| 53 | Extended defects in GaN nanocolumns characterized by cathodoluminescence directly performed in a transmission electron microscope. Turkish Journal of Physics, 2014, 38, 323-327. | 1.1 | 0 |
| 54 | <i>In situ</i> anodization of aluminum surfaces studied by x-ray reflectivity and electrochemical impedance spectroscopy. Journal of Applied Physics, 2014, 116, . | 2.5 | 17 |

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|----|--|-----|-----------|
| 55 | Determination of carrier diffusion length in p- and n-type GaN. , 2014, , . | | 3 |
| 56 | Optical properties of <i>m</i> -plane GaN grown on patterned Si(112) substrates by MOCVD using a two-step approach. Proceedings of SPIE, 2014, , . | 0.8 | 1 |
| 57 | Impact of extended defects on optical properties of (1-101)GaN grown on patterned Si. Proceedings of SPIE, 2014, , . | 0.8 | 1 |
| 58 | Spatially resolved optical emission of cubic GaN/AlN multi-quantum well structures. Materials Research Society Symposia Proceedings, 2014, 1736, 25. | 0.1 | 2 |
| 59 | Growth of InGaN/GaN core-shell structures on selectively etched GaN rods by molecular beam epitaxy. Journal of Crystal Growth, 2014, 392, 5-10. | 1.5 | 13 |
| 60 | Symmetry dependent optoelectronic properties of grain boundaries in polycrystalline Cu(In,Ga)Se ₂ thin films. Journal of Applied Physics, 2014, 115, 023514. | 2.5 | 12 |
| 61 | InGaN: Direct correlation of nanoscopic morphology features with optical and structural properties. Applied Physics Letters, 2014, 105, 072108. | 3.3 | 6 |
| 62 | Nano-scale luminescence characterization of individual InGaN/GaN quantum wells stacked in a microcavity using scanning transmission electron microscope cathodoluminescence. Applied Physics Letters, 2014, 105, 032101. | 3.3 | 30 |
| 63 | Group III nitride core-shell nano- and microrods for optoelectronic applications. Physica Status Solidi - Rapid Research Letters, 2013, 7, 800-814. | 2.4 | 76 |
| 64 | Investigation of vertical compositional gradients in Cu(In,Ga)Se ₂ by highly spatially and spectrally resolved cathodoluminescence microscopy. Thin Solid Films, 2013, 535, 270-274. | 1.8 | 9 |
| 65 | Green to blue polarization compensated c-axis oriented multi-quantum wells by AlGaInN barrier layers. Applied Physics Letters, 2013, 102, . | 3.3 | 13 |
| 66 | Depth distribution of carrier lifetimes in semipolar (11̄01) GaN grown by MOCVD on patterned Si substrates. Proceedings of SPIE, 2013, , . | 0.8 | 0 |
| 67 | MOVPE growth of semi-polar GaN light-emitting diode structures on planar Si(112) and Si(113) substrates. Journal of Crystal Growth, 2013, 370, 288-292. | 1.5 | 15 |
| 68 | Optical studies of strain and defect distribution in semipolar (11̄01) GaN on patterned Si substrates. Journal of Applied Physics, 2013, 114, 113502. | 2.5 | 25 |
| 69 | GaN laser structure with semipolar quantum wells and embedded nanostripes. , 2013, , . | | 0 |
| 70 | Microscopic distribution of extended defects and blockage of threading dislocations by stacking faults in semipolar (11̄01) GaN revealed from spatially resolved luminescence. Applied Physics Letters, 2013, 103, . | 3.3 | 11 |
| 71 | GaN-Based Vertical Cavities with All Dielectric Reflectors by Epitaxial Lateral Overgrowth. Japanese Journal of Applied Physics, 2013, 52, 08JH03. | 1.5 | 6 |
| 72 | An improved carrier rate model to evaluate internal quantum efficiency and analyze efficiency droop origin of InGaN based light-emitting diodes. Journal of Applied Physics, 2012, 112, 023107. | 2.5 | 53 |

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|----|---|-----|-----------|
| 73 | Excitonic transport in ZnO. Proceedings of SPIE, 2012, , . | 0.8 | 1 |
| 74 | Direct nano-scale correlation of structural and optical properties of lattice matched AlInN/AlGaN DBRs using helium temperature scanning transmission electron microscopy cathodoluminescence. Microscopy and Microanalysis, 2012, 18, 1874-1875. | 0.4 | 1 |
| 75 | Direct imaging of GaN Pyramids covered by InGaN Single Quantum Well using nano-scale Scanning Transmission Electron Microscopy Cathodoluminescence. Microscopy and Microanalysis, 2012, 18, 1838-1839. | 0.4 | 1 |
| 76 | Highly spatially resolved Cathodoluminescence of Single GaN Quantum Dots directly performed in a Scanning Transmission Electron Microscope. Microscopy and Microanalysis, 2012, 18, 1878-1879. | 0.4 | 2 |
| 77 | Excitonic transport in ZnO. Journal of Materials Research, 2012, 27, 2225-2231. | 2.6 | 21 |
| 78 | Single-photon emission from electrically driven InP quantum dots epitaxially grown on CMOS-compatible Si(001). Nanotechnology, 2012, 23, 335201. | 2.6 | 10 |
| 79 | Effect of MOCVD growth conditions on the optical properties of semipolar (1-101) GaN on Si patterned substrates. Proceedings of SPIE, 2012, , . | 0.8 | 4 |
| 80 | Cathodoluminescence directly performed in a transmission electron microscope: nanoscale correlation of structural and optical properties. Microscopy and Microanalysis, 2012, 18, 1834-1835. | 0.4 | 1 |
| 81 | Semipolar GaInN quantum well structures on large area substrates. Physica Status Solidi (B): Basic Research, 2012, 249, 464-467. | 1.5 | 7 |
| 82 | Growth and stacking fault reduction in semi-polar GaN films on planar Si(112) and Si(113). Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 507-510. | 0.8 | 16 |
| 83 | Comprehensive Comparison of Various Techniques for the Analysis of Elemental Distributions in Thin Films. Microscopy and Microanalysis, 2011, 17, 728-751. | 0.4 | 72 |
| 84 | MOVPE of CuGaSe ₂ on GaAs in the presence of a CuxSe secondary phase. Journal of Crystal Growth, 2011, 315, 82-86. | 1.5 | 14 |
| 85 | Indium incorporation in GaInN/GaN quantum well structures on polar and nonpolar surfaces. Physica Status Solidi (B): Basic Research, 2011, 248, 600-604. | 1.5 | 15 |
| 86 | Growth and coalescence behavior of semipolar $(1\bar{1}\bar{2})$ GaN on pre-structured \bar{r} -plane sapphire substrates. Physica Status Solidi (B): Basic Research, 2011, 248, 588-593. | 1.5 | 34 |
| 87 | Three-dimensional GaN for semipolar light emitters. Physica Status Solidi (B): Basic Research, 2011, 248, 549-560. | 1.5 | 62 |
| 88 | High wavelength tunability of InGaN quantum wells grown on semipolar GaN pyramid facets. Physica Status Solidi (B): Basic Research, 2011, 248, 605-610. | 1.5 | 21 |
| 89 | Spectrally and time-resolved cathodoluminescence microscopy of semipolar InGaN SQW on $(\bar{1}\bar{1}\bar{2})$ and $(1\bar{1}\bar{1})$ pyramid facets. Physica Status Solidi (B): Basic Research, 2011, 248, 632-637. | 1.5 | 12 |
| 90 | Spectral features in different sized InGaN/GaN micropylramids. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2387-2389. | 0.8 | 2 |

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| 91 | Epitaxial lateral overgrowth of non-polar GaN(111̄,00) on Si(112) patterned substrates by MOCVD. Journal of Crystal Growth, 2011, 314, 129-135. | 1.5 | 20 |
| 92 | Anti-phase domains in cubic GaN. Journal of Applied Physics, 2011, 110, . | 2.5 | 26 |
| 93 | Eliminating stacking faults in semi-polar GaN by AlN interlayers. Applied Physics Letters, 2011, 99, 021905. | 3.3 | 22 |
| 94 | Optical properties of nonpolar (1-100) and semipolar (1-101)GaN grown by MOCVD on Si patterned substrates. Proceedings of SPIE, 2011, , . | 0.8 | 5 |
| 95 | Well width study of InGaN multiple quantum wells for blue-green emitter. Journal of Crystal Growth, 2010, 312, 3428-3433. | 1.5 | 10 |
| 96 | GaNN-based LED structures on selectively grown semi-polar crystal facets. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1407-1413. | 1.8 | 22 |
| 97 | Semipolar GaInN/GaN light-emitting diodes grown on honeycomb patterned substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2140-2143. | 0.8 | 27 |
| 98 | Luminescence Properties of Photonic Crystal InGaN/GaN Light Emitting Layers on Silicon-on-Insulator. Electrochemical and Solid-State Letters, 2010, 13, H343. | 2.2 | 6 |
| 99 | Structure and luminescence of (Ca,Sr)2SiS4Eu ²⁺ phosphors. Journal Physics D: Applied Physics, 2010, 43, 085401. | 2.8 | 29 |
| 100 | AlInN/GaN based multi quantum well structures growth and optical properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S451. | 0.8 | 11 |
| 101 | MOVPE growth of high-quality Al _{0.1} Ga _{0.9} N on Si(111) substrates for UV LEDs. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S455. | 0.8 | 3 |
| 102 | Microstructural anisotropy of a-plane GaN analyzed by high resolution X-ray diffraction. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S498. | 0.8 | 12 |
| 103 | Fabrication and optical properties of C ₆₀ -SiC/Si hybrid rolled-up microtubes. Journal of Applied Physics, 2009, 105, 016103. | 2.5 | 13 |
| 104 | Fabrication, Self-Assembly, and Properties of Ultrathin AlN/GaN Porous Crystalline Nanomembranes: Tubes, Spirals, and Curved Sheets. ACS Nano, 2009, 3, 1663-1668. | 14.6 | 91 |
| 105 | Analysis of point defects in AlN epilayers by cathodoluminescence spectroscopy. Applied Physics Letters, 2009, 95, . | 3.3 | 28 |
| 106 | Growth of QW structures with high indium concentration on -plane and -plane surfaces by MOVPE. Journal of Crystal Growth, 2008, 310, 4987-4991. | 1.5 | 6 |
| 107 | Microscopic recombination kinetics in high quality, fully coalesced a-plane GaN ELO structures investigated by ps-time-resolved cathodoluminescence microscopy. , 2008, , . | | 0 |
| 108 | A -plane GaN epitaxial lateral overgrowth structures: Growth domains, morphological defects, and impurity incorporation directly imaged by cathodoluminescence microscopy. Applied Physics Letters, 2008, 92, . | 3.3 | 35 |

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|-----|---|------|-----------|
| 109 | Time-resolved cathodoluminescence of Mg-doped GaN. Applied Physics Letters, 2008, 93, . | 3.3 | 19 |
| 110 | Effect of the growth temperature and the AlN mole fraction on In incorporation and properties of quaternary III-nitride layers grown by molecular beam epitaxy. Journal of Applied Physics, 2008, 104, 083510. | 2.5 | 16 |
| 111 | Metalorganic vapor phase epitaxy of ZnO: towards p-type conductivity. , 2007, 6474, 32. | | 9 |
| 112 | Thin film growth of ZnO and its relation to substrate properties. , 2007, , . | | 0 |
| 113 | Complex excitonic recombination kinetics in ZnO: Capture, relaxation, and recombination from steady state. Applied Physics Letters, 2007, 90, 041917. | 3.3 | 31 |
| 114 | Blue light emitting diodes on Si(001) grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 41-44. | 0.8 | 4 |
| 115 | Laser-Interference Lithography Tailored for Highly Symmetrically Arranged ZnO Nanowire Arrays. Small, 2007, 3, 76-80. | 10.0 | 95 |
| 116 | Homoepitaxy of ZnO: from the substrates to doping. Physica Status Solidi (B): Basic Research, 2007, 244, 1451-1457. | 1.5 | 23 |
| 117 | Vapour transport growth of ZnO nanorods. Applied Physics A: Materials Science and Processing, 2007, 88, 17-20. | 2.3 | 16 |
| 118 | Direct imaging of phase separation in ZnCdO layers. Applied Physics Letters, 2006, 88, 061915. | 3.3 | 55 |
| 119 | Catalyst-free vapor-phase transport growth of vertically aligned ZnO nanorods on 6H-SiC and (11-20)Al ₂ O ₃ . Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1046-1050. | 0.8 | 35 |
| 120 | MBE growth of ZnO layers on sapphire employing hydrogen peroxide as an oxidant. Journal of Crystal Growth, 2006, 287, 7-11. | 1.5 | 39 |
| 121 | MOVPE growth of high-quality AlN. Journal of Crystal Growth, 2006, 297, 306-310. | 1.5 | 68 |
| 122 | Growth and Characterization of Homoepitaxial ZnO Thin Films Grown by CVD. Materials Research Society Symposia Proceedings, 2006, 957, 1. | 0.1 | 0 |
| 123 | Microscopic Luminescence Properties of ZnO and ZnO Based Heterostructures. Acta Physica Polonica A, 2006, 110, 103-110. | 0.5 | 1 |
| 124 | ZnO MOVPE growth: From local impurity incorporation towards p-type doping. Superlattices and Microstructures, 2005, 38, 245-255. | 3.1 | 27 |
| 125 | Localization versus carrier-screening effects in InGaN quantum wells – A time-resolved cathodoluminescence study. AIP Conference Proceedings, 2005, , . | 0.4 | 1 |
| 126 | Local luminescence of ZnO nanowire-covered surface: A cathodoluminescence microscopy study. Applied Physics Letters, 2005, 86, 023113. | 3.3 | 43 |

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|-----|---|-----|-----------|
| 127 | Microscopic Spatial Distribution of Bound Excitons in High-Quality ZnO. Materials Science Forum, 2005, 483-485, 1065-0. | 0.3 | 0 |
| 128 | Localization versus field effects in single InGaN quantum wells. Applied Physics Letters, 2004, 84, 58-60. | 3.3 | 36 |
| 129 | Ostwald ripening and flattening of epitaxial ZnO layers during in situ annealing in metalorganic vapor phase epitaxy. Applied Physics Letters, 2004, 85, 1496-1498. | 3.3 | 39 |
| 130 | Direct evidence for selective impurity incorporation at the crystal domain boundaries in epitaxial ZnO layers. Applied Physics Letters, 2004, 85, 1976-1978. | 3.3 | 13 |
| 131 | Self-assembly of ZnO nanowires and the spatial resolved characterization of their luminescence. Nanotechnology, 2004, 15, 1401-1404. | 2.6 | 52 |
| 132 | Microscopic spatial distribution of bound excitons in high-quality ZnO. Journal of Crystal Growth, 2004, 272, 785-788. | 1.5 | 4 |
| 133 | Bound exciton and donor-acceptor pair recombinations in ZnO. Physica Status Solidi (B): Basic Research, 2004, 241, 231-260. | 1.5 | 1,499 |
| 134 | A two-step metal organic vapor phase epitaxy growth method for high-quality ZnO on GaN/Al ₂ O ₃ (0001). Journal of Crystal Growth, 2004, 267, 140-144. | 1.5 | 52 |
| 135 | Heteroepitaxy and nitrogen doping of high-quality ZnO. Journal of Crystal Growth, 2004, 272, 800-804. | 1.5 | 16 |
| 136 | Metalorganic chemical vapor phase deposition of ZnO with different O-precursors. Journal of Crystal Growth, 2003, 248, 14-19. | 1.5 | 46 |
| 137 | MOVPE growth of GaN on Si(111) substrates. Journal of Crystal Growth, 2003, 248, 556-562. | 1.5 | 125 |
| 138 | Variation of structural and optical properties across an AlGaN/GaN HEMT structure directly imaged by cathodoluminescence microscopy. Physica Status Solidi A, 2003, 200, 183-186. | 1.7 | 0 |
| 139 | Metalorganic chemical vapor phase epitaxy of gallium-nitride on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1583-1606. | 0.8 | 116 |
| 140 | Gallium-nitride-based devices on silicon. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1940-1949. | 0.8 | 18 |
| 141 | Optical micro-characterization of group-III-nitrides: correlation of structural, electronic and optical properties. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1795-1815. | 0.8 | 12 |
| 142 | The origin of the PL photoluminescence Stokes shift in ternary group-III nitrides: field effects and localization. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1835-1845. | 0.8 | 15 |
| 143 | Optical and structural analysis of ZnCdO layers grown by metalorganic vapor-phase epitaxy. Applied Physics Letters, 2003, 83, 3290-3292. | 3.3 | 174 |
| 144 | Metal Organic Vapor Phase Epitaxy of ZnO on GaN/Si(111) Using Tertiary-Butanol as O-Precursor. Japanese Journal of Applied Physics, 2003, 42, 7474-7477. | 1.5 | 23 |

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|-----|---|-----|-----------|
| 145 | Optical evaluation of pretreated InGaN quantum well structures. Materials Research Society Symposia Proceedings, 2003, 798, 598. | 0.1 | 1 |
| 146 | Non-planar Selective Area Growth and Characterization of GaN and AlGaIn. Japanese Journal of Applied Physics, 2003, 42, 6276-6283. | 1.5 | 24 |
| 147 | Microscopic correlation of redshifted luminescence and surface defects in thick In _x Ga _{1-x} N layers. Applied Physics Letters, 2002, 80, 3524-3526. | 3.3 | 21 |
| 148 | Response to "Comment on "Low Stokes shift in thick and homogeneous InGaIn epilayers" [Appl. Phys. Lett 81, 1353 (2002)]. Applied Physics Letters, 2002, 81, 1355-1356. | 3.3 | 1 |
| 149 | Low Stokes shift in thick and homogeneous InGaIn epilayers. Applied Physics Letters, 2002, 80, 550-552. | 3.3 | 58 |
| 150 | High Quality GaN Grown by Facet-Controlled ELO (FACELO) Technique. Physica Status Solidi A, 2002, 194, 545-549. | 1.7 | 18 |
| 151 | Spatial variation of luminescence of InGaIn alloys measured by highly-spatially-resolved scanning cathodoluminescence. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 93, 19-23. | 3.5 | 10 |
| 152 | Spatial Variation of Luminescence of InGaIn Alloys Measured by Highly-Spatially-Resolved Scanning Cathodoluminescence. Physica Status Solidi (B): Basic Research, 2001, 228, 35-39. | 1.5 | 10 |
| 153 | A Comparison of Rutherford Backscattering Spectroscopy and X-Ray Diffraction to Determine the Composition of Thick InGaIn Epilayers. Physica Status Solidi (B): Basic Research, 2001, 228, 41-44. | 1.5 | 23 |
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